



DCR680N85

Phase Control Thyristor

Replaces DS5935-4 DS5935-5 May 2024 (LN43323)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Medium Voltage Soft Starts
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		$T_{vj} = -40^{\circ}C$ to 125°C,
DCR680N85*	8500	IDRM = IRRM = 200mA,
DCR680N80	8000	VDRM, VRRM tp = 10ms
DCR680N75	7500	VDSM & VRSM =
DCR680N70	7000	VDRM & VRRM + 100V
		respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR680N85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	8500V
I _{T(AV)}	680A
Ітѕм	9800A
dV/dt*	1500V/µs
dl/dt	200A/μs

^{*} Higher dV/dt selections are available on request

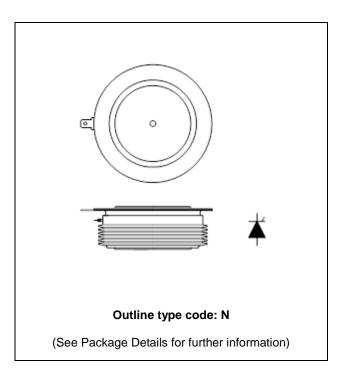


Fig. 1 Package outline

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^{*8200}V @ -40°C, 8500V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol Parameter Test Condi		Test Conditions	Max.	Units
Double Side Cooled				
IT(AV)	Mean on-state current	Half wave resistive load	680	А
IT(RMS)	RMS value	-	1070	А
lτ	Continuous (direct) on-state current	-	1020	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	9.8	kA
l²t	I2t for fusing	V _R = 0	0.48	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
		Double side cooled	DC	-	22.0	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cingle side socied	Anode DC	-	40.5	°C/kW
		Single side cooled	Cathode DC	-	50.1	°C/kW
D	The second are interest and the state in large	Clamping force 23kN	Double side	-	4.0	°C/kW
Rth(c-h)	Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	8.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Fm Clamping force			20	25	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	ns	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	-	200	mA	
Vтм	Instantaneous forward voltage	At 2900A peak, Tj = 25°C		3.65	4.30	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% VDRM, Tj = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω	Repetitive 50Hz	-	100	A/µs
	Nate of fise of off-state current	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	200	A/µs
V	Threshold voltage - Low level	100A to 500A at Tcase = 12	25°C	-	1.03	٧
V T(TO)	Threshold voltage - High level 500A to 2500A at Tcase = 125°C		25°C	-	1.30	V
	On-state slope resistance - Low level	100A to 500A at Tcase = 125°C		-	2.08	mΩ
ľΤ	On-state slope resistance - High level	500A to 2500A at Tcase = 125°C		-	1.55	mΩ
tgd	Delay time	$V_D = 67\% \ V_{DRM}$, gate source 30V, 10Ω $t_r = 0.5 \mu s$, $T_j = 25 ^{\circ} C$			3	μs
tq	Turn-off time	$T_{\rm j} = 125 {\rm ^{\circ}C}$, Ipeak = 1000A, tp = 1000 μ s, $V_{\rm RM} = 100 {\rm V}$, dI/dt = 5A/ μ s, $dV_{\rm DR}/dt = 20 {\rm V}/\mu$ s linear to 2500V		-	1200	μs
Qs	Stored charge	Iτ = 1000A, t _P = 1000μs, T _j =	= 125°C,	3000	4000	μC
IRR	Reverse recovery current	$dI/dt = 5A/\mu s$, VR peak = 100V. [LEM]		90	120	Α
Qs	Stored charge	Tj = 125°C, dl/dt = 1A/µs,		(Тур).) 3160	μC
IRR	Reverse recovery current	VR peak ~ 4400V, VR ~ 2600V		(Typ.) 40		Α
I L	Latching current	$T_j = 25$ °C, $V_D = 5V$	-	3	Α	
Ін	Holding current	Tj = 25°C, Rg-к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V _{GD}	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
lgт	Gate trigger current	VDRM = 5V, Tcase = 25°C	350	mA
Igo	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	15	mA

CURVES

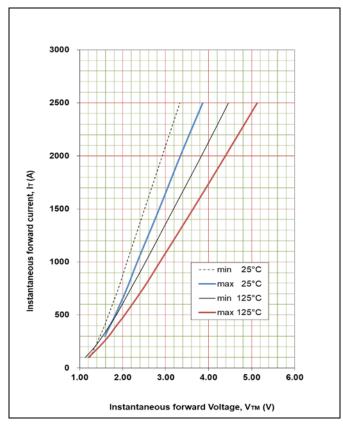


Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

 $V_{TM} = A + B.In(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.263791

B = 0.175445

C = 0.001404

D = -0.000328

These values are valid for $T_j = 125^{\circ}C$ for I_{T} 100A to 2500A

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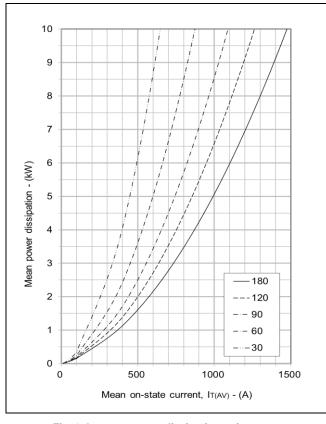


Fig. 3 On-state power dissipation - sine wave

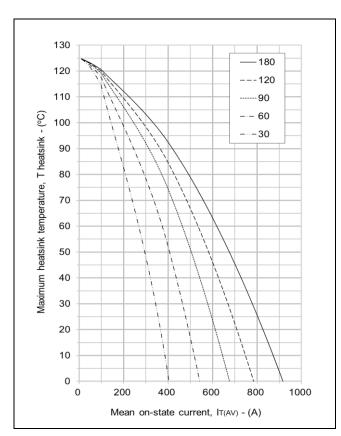


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

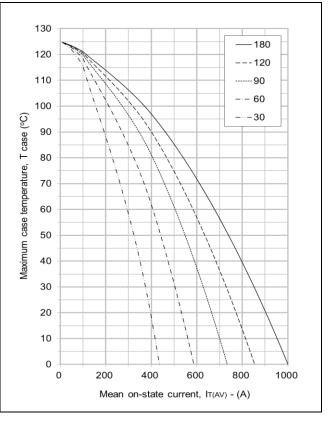


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

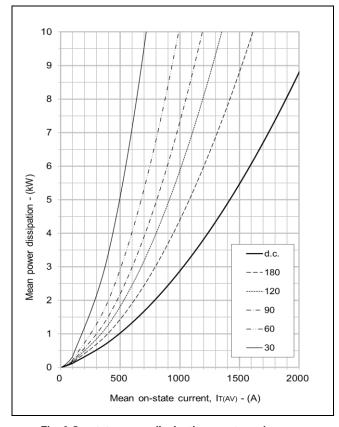


Fig. 6 On-state power dissipation - rectangular wave

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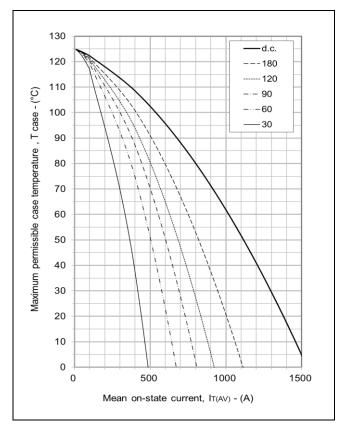
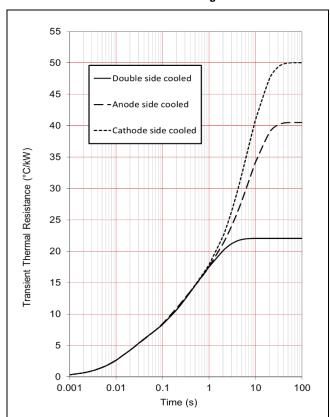


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



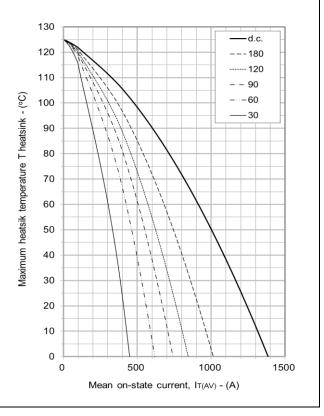


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	3.473	4.905	9.146	4.522
cooled	Ti(s)	0.146	0.017	1.283	0.377
Anode side	Ri(°C/kW)	6.039	4.278	5.130	25.087
cooled	Ti(s)	0.136	0.014	0.659	7.236
Cathode side	Ri(°C/kW)	7.667	5.053	9.736	27.599
cooled	Ti(s)	0.224	0.017	4.057	8.278

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th(j-c)}}$ when the device operates at conduction angles other than d.c.

	Double side co	oling
	ΔZ _{th} (z)
θ°	sine.	rect.
180	3.03	2.07
120	3.49	2.95
90	3.99	3.43
60	4.43	3.94
30	4.77	4.49
15	4 92	4.77

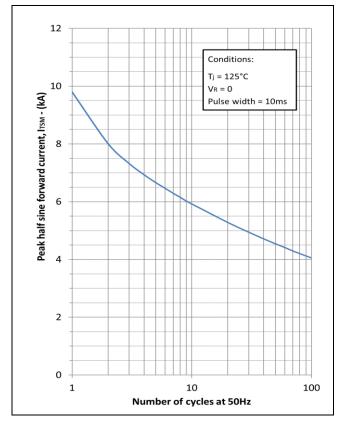
	Arroad dide Coolling			 	tillode Oldet	2 COOIIIIQ
		ΔZ_{th} (z)			ΔZ_t	h (Z)
	θ°	sine.	rect.	θ°	sine.	rect.
	180	3.03	2.07	180	3.12	2.12
	120	3.49	2.95	120	3.61	3.04
	90	3.99	3.43	90	4.13	3.54
	60	4.43	3.94	60	4.60	4.08
	30	4.76	4.48	30	4.96	4.66
	15	4.92	4.77	15	5.13	4.97

	Anode Side	ode Side Cooling Cathode Sided Cooling								
	ΔZ_{th} (z)				ΔZ_t	h (Z)				
9°	sine. rect.			θ°	sine.	rect.				
80	3.03	2.07	1	180	3.12	2.12				
20	3.49	2.95		120	3.61	3.04				
90	3.99	3.43		90	4.13	3.54				
60	4.43 3.94			60	4.60	4.08				
30	4.76	4.48		30	4.96	4.66				
15	4.02	4.77	1	15	E 12	4.07				

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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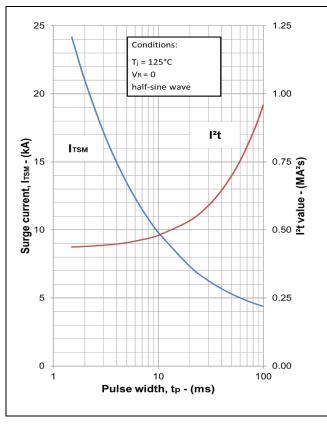


Fig. 10 Multi-cycle surge current

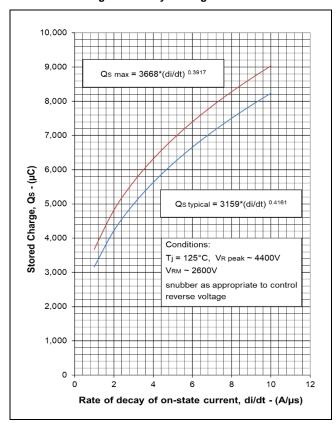


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

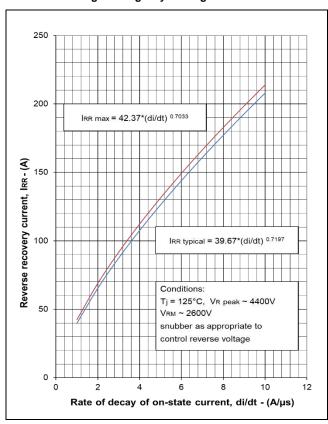


Fig. 13 Reverse recovery current

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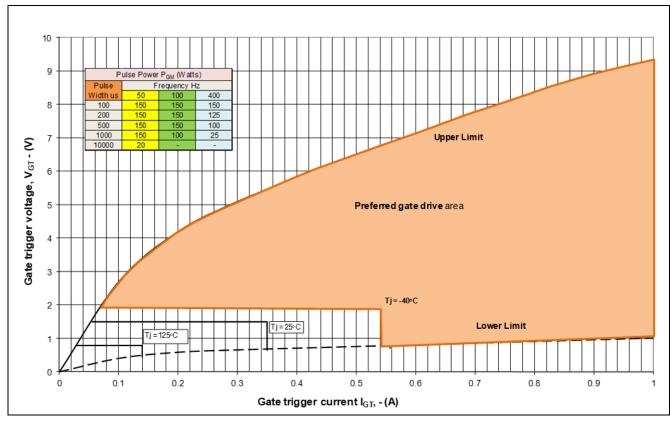


Fig. 14 Gate characteristics

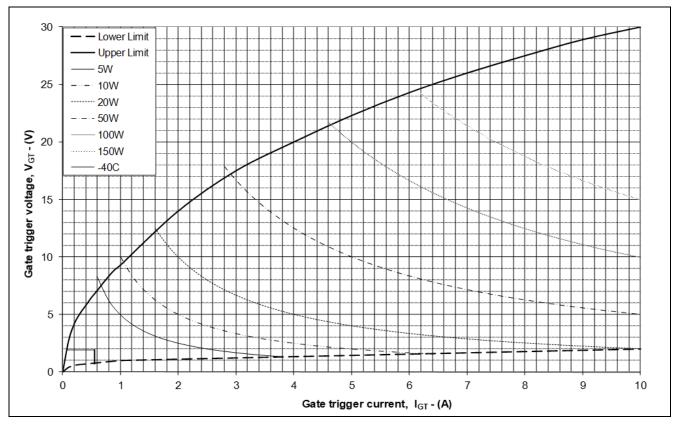


Fig. 15 Gate characteristics

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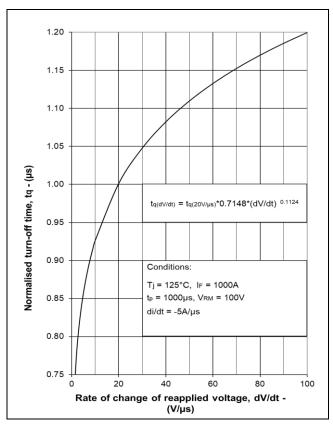


Fig. 16 Turn-off time

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PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

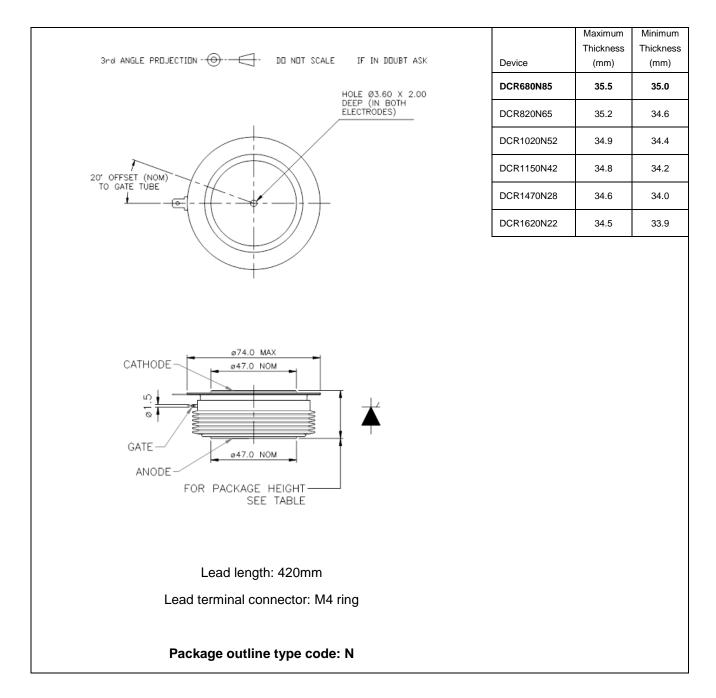


Fig. 17 Package outline

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